

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	1.7m Ω @10V	300A

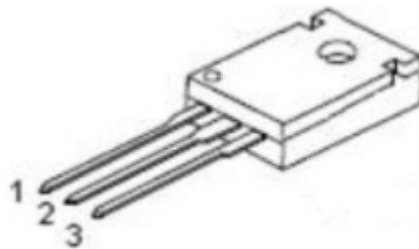
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

Application

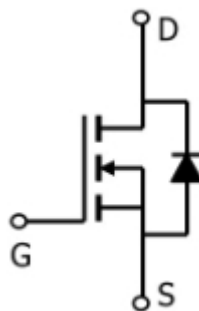
- Power switching application
- DC-DC Converter
- Power Management

Package

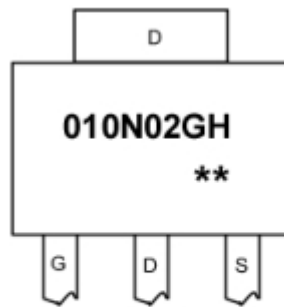


TO-247(1:G 2:D 3:S)

Circuit diagram



Marking



010N02GH : Product code
****** : Week code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (T _C =25°C)	I _D	300	A
Pulsed Drain Current	I _{DM}	1200	A
Total Power Dissipation(T _C =25°C)	P _D	360	W
Single Pulse Avalanche Energy ¹	E _{AS}	550	mJ
Thermal Resistance Junction-Case	R _{θJC}	0.34	°C/ W
Operation and storage temperature	T _{STG} , T _J	-55~ +150	°C

Electrical characteristics

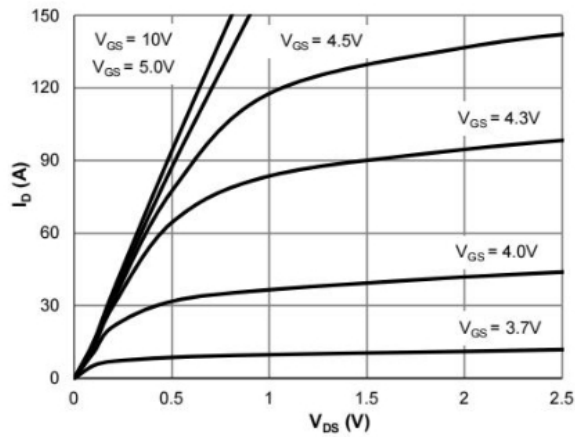
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	100			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V,V _{GS} = 0V			1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±0.1	uA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	2.7	4	V
Drain-Source on-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		1.9	2.2	Ω
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, f=1MHz		9625		pF
Output Capacitance	C _{Oss}			1608		
Reverse Transfer Capacitance	C _{rss}			75		
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =20A		160		nC
Gate-Source Charge	Q _{gS}			31		
Gate-Drain Charge	Q _{gd}			37		
Turn-On Delay Time	T _{d(on)}	V _{GS} =10V, V _{DS} =50V, R _L =2.5Ω, R _G =6.0Ω		35		nS
Rise Time	T _r			68		
Turn-Off Delay Time	T _{d(off)}			150		
Fall Time	T _f			105		
Diode Characteristics						
Diode Forward Voltage2	V _{SD}	V _{GS} =0V, I _S =1A			1.2	V

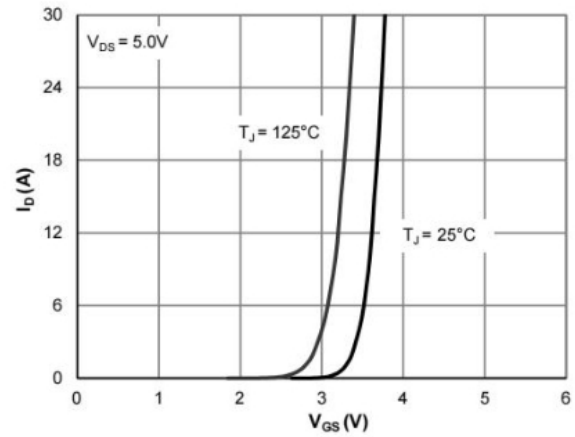
Notes:

1. E AS is tested at starting $T_j = 25^{\circ}\text{C}$, $V_{DD} = 50V, V_{GS} = 10V, L = 0.1mH, R_g = 25 m\Omega$;

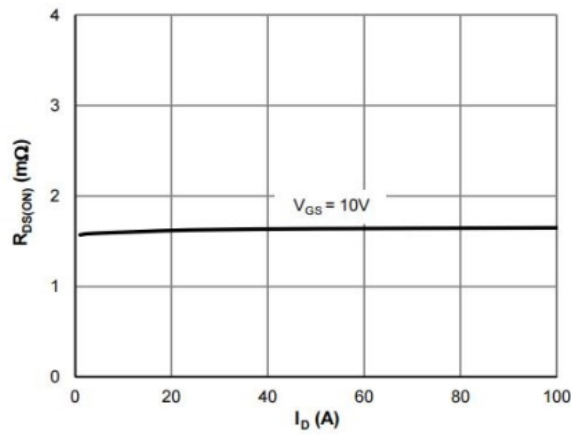
Typical Characteristics



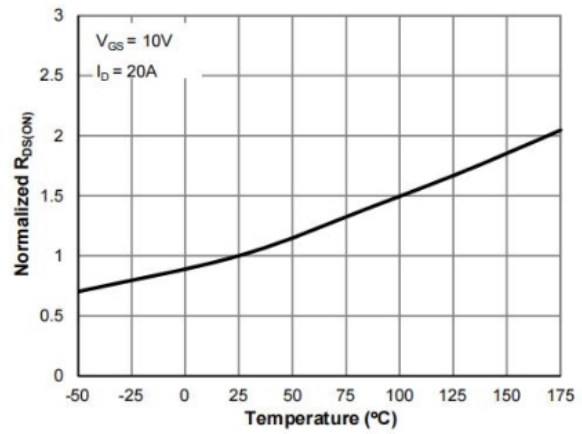
Typical Output Characteristics



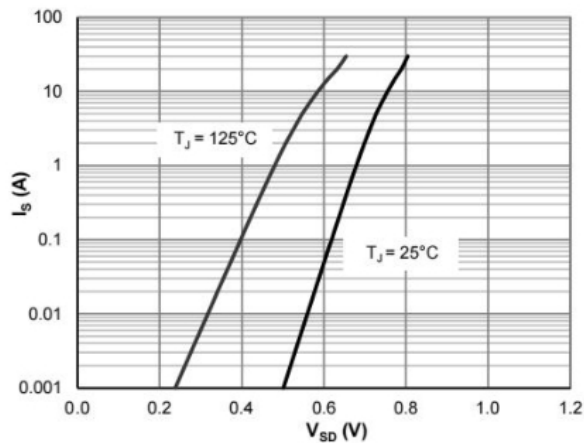
Transfer Characteristics



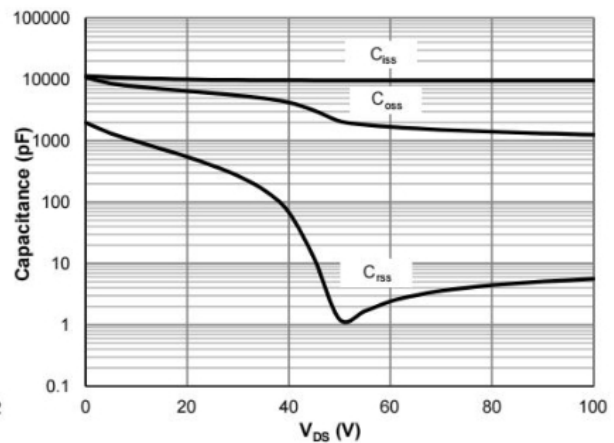
On-Resistance vs. Drain Current



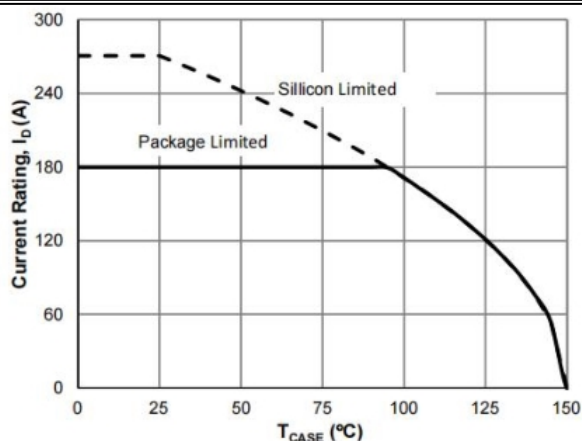
On-Resistance vs. Junction Temperature



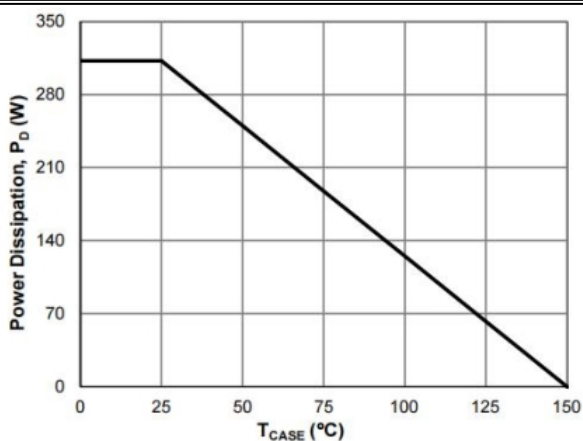
Body-Diode Characteristics



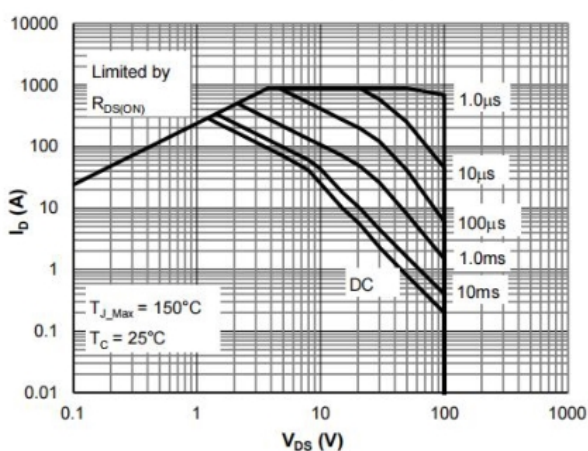
Capacitance Characteristics



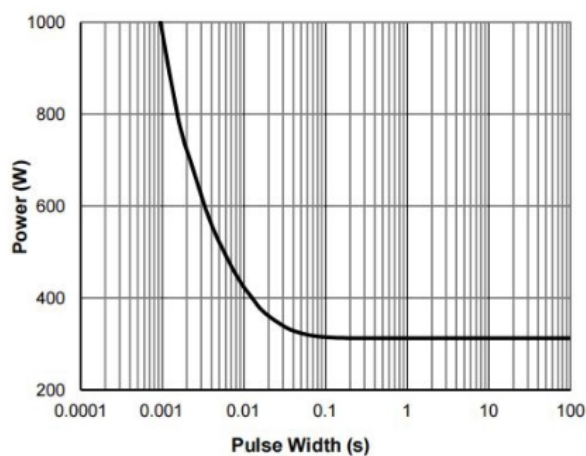
Current De-rating



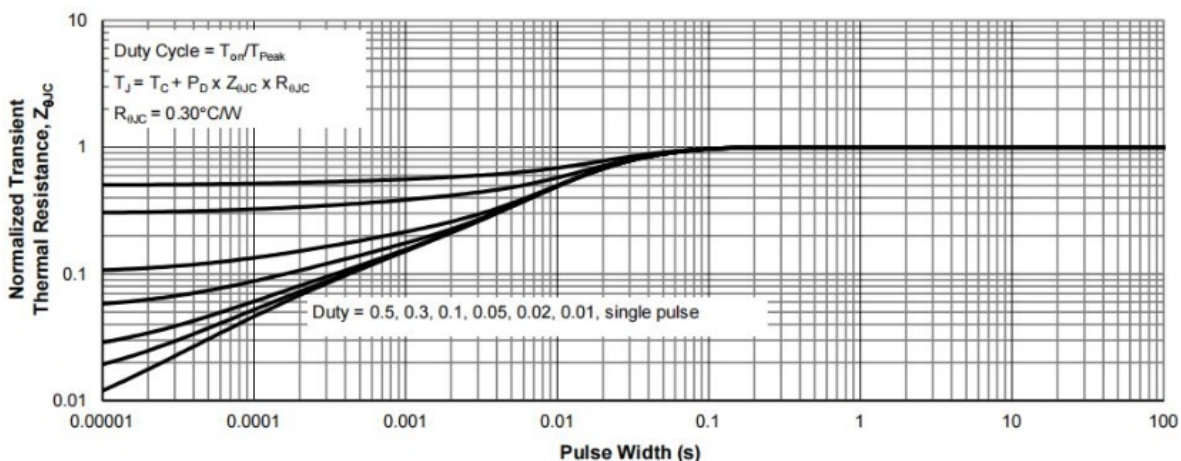
Power De-rating



Maximum Safe Operating Area

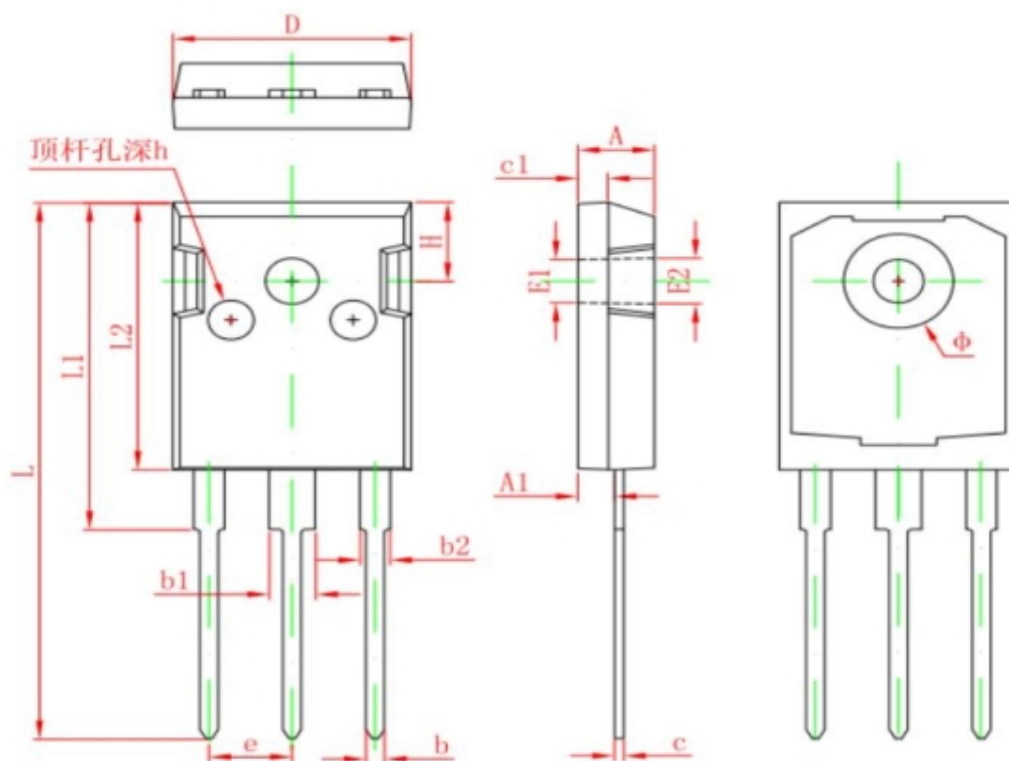


Single Pulse Power Rating, Junction-to-Case



Normalized Maximum Transient Thermal Impedance

TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF.		0.138 REF.	
E2	3.600 REF.		0.142 REF.	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
φ	7.100	7.300	0.280	0.287
e	5.450 TYP.		0.215 TYP.	
H	5.980 REF.		0.235 REF.	
h	0.000	0.300	0.000	0.012